

To all our customers

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The semiconductor operations of Hitachi and Mitsubishi Electric were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Mitsubishi Electric, Mitsubishi Electric Corporation, Mitsubishi Semiconductors, and other Mitsubishi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Note : Mitsubishi Electric will continue the business operations of high frequency & optical devices and power devices.

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

DESCRIPTION

The M5M5V108DFP,VP,KV are a 1048576-bit CMOS static RAM organized as 131072 word by 8-bit which are fabricated using high-performance triple-polysilicon and double metal CMOS technology. The use of thin film transistor (TFT) load cells and CMOS periphery result in a high density and low power static RAM.

They are low standby current and low operation current and ideal for the battery back-up application.

The M5M5V108DVP,KV are packaged in a 32-pin thin small outline package which is a high reliability and high density surface mount device(SMD).

FEATURES

Type name	Access time (max)	Vcc	Power supply current	
			Active (1MHz) (max)	stand-by (max)
M5M5V108DFP,VP,KV-70HI	70ns	2.7~3.6V	5mA	24 μ A

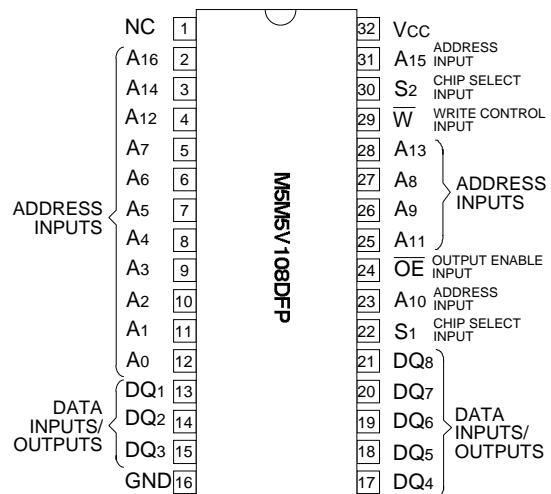
- Directly TTL compatible : All inputs and outputs
- Easy memory expansion and power down by \bar{S}_1, \bar{S}_2
- Data hold on +2V power supply
- Three-state outputs : OR - tie capability
- \bar{OE} prevents data contention in the I/O bus
- Common data I/O
- Package

M5M5V108DFP 32pin 525mil SOP
M5M5V108DVP,RV 32pin 8 X 20 mm² TSOP
M5M5V108DKV,KR 32pin 8 X 13.4 mm² TSOP

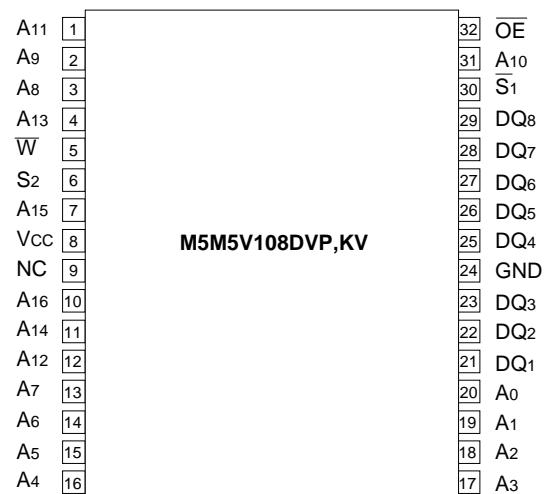
APPLICATION

Small capacity memory units

PIN CONFIGURATION (TOP VIEW)



Outline 32P2M-A



Outline 32P3H-E(VP), 32P3K-B(KV)

NC : NO CONNECTION

FUNCTION

The operation mode of the M5M5V108D series are determined by a combination of the device control inputs \bar{S}_1 , S_2 , \bar{W} and OE .

Each mode is summarized in the function table.

A write cycle is executed whenever the low level \bar{W} overlaps with the low level \bar{S}_1 and the high level S_2 . The address must be set up before the write cycle and must be stable during the entire cycle. The data is latched into a cell on the trailing edge of \bar{W} , \bar{S}_1 or S_2 , whichever occurs first, requiring the set-up and hold time relative to these edge to be maintained. The output enable input OE directly controls the output stage. Setting the OE at a high level, the output stage is in a high-impedance state, and the data bus contention problem in the write cycle is eliminated.

A read cycle is executed by setting \bar{W} at a high level and OE at a low level while \bar{S}_1 and S_2 are in an active state ($S_1=L$, $S_2=H$).

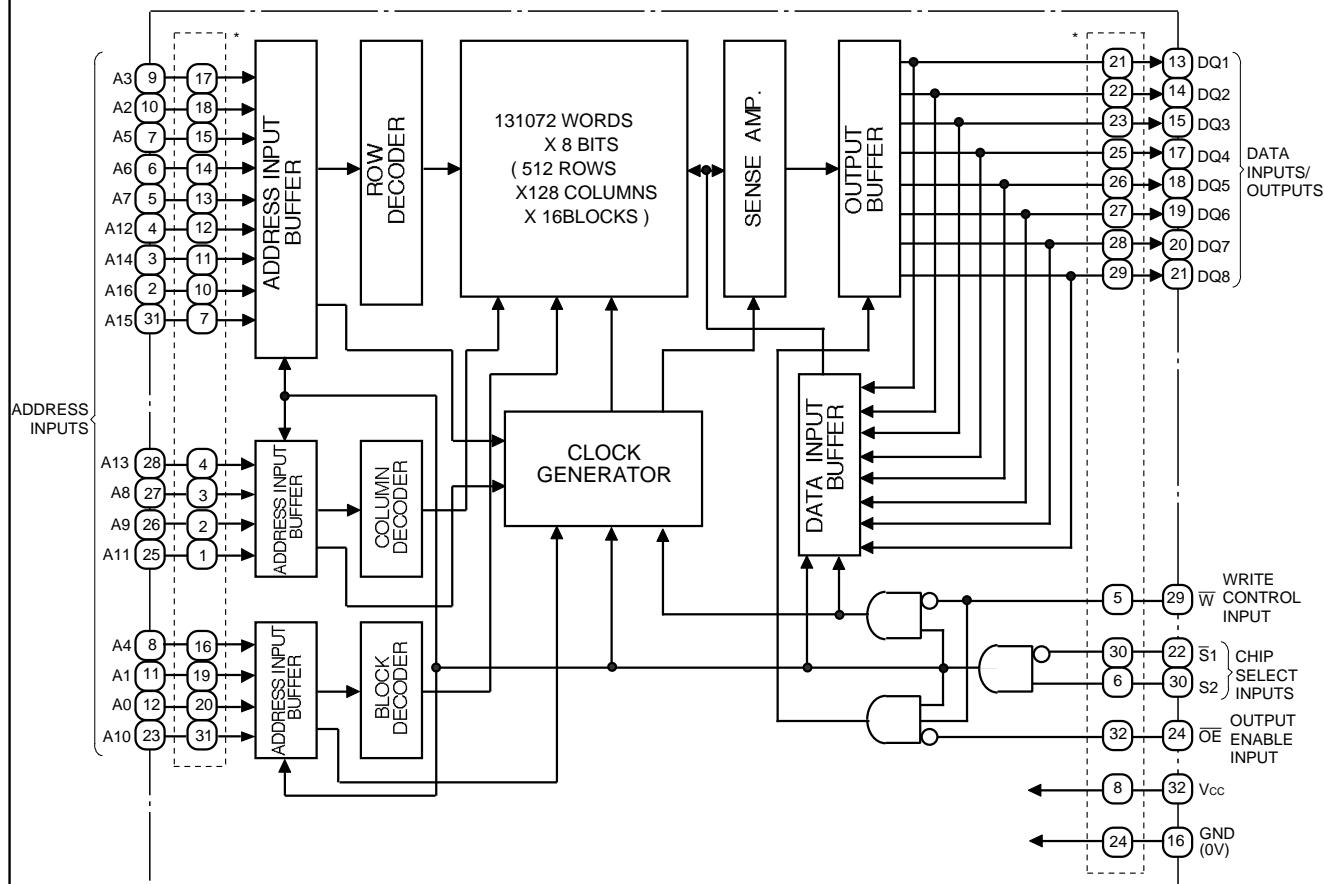
FUNCTION TABLE

\bar{S}_1	S_2	\bar{W}	OE	Mode	DQ	Icc
X	L	X	X	Non selection	High-impedance	Stand-by
H	X	X	X	Non selection	High-impedance	Stand-by
L	H	L	X	Write	Din	Active
L	H	H	L	Read	Dout	Active
L	H	H	H		High-impedance	Active

Note 1: "H" and "L" in this table mean VIH and VIL, respectively.
 2: "X" in this table should be "H" or "L".

When setting \bar{S}_1 at a high level or S_2 at a low level, the chip are in a non-selectable mode in which both reading and writing are disabled. In this mode, the output stage is in a high-impedance state, allowing OR-tie with other chips and memory expansion by \bar{S}_1 and S_2 . The power supply current is reduced as low as the stand-by current which is specified as I_{CC3} or I_{CC4} , and the memory data can be held at +2V power supply, enabling battery back-up operation during power failure or power-down operation in the non-selected mode.

BLOCK DIAGRAM



* Pin numbers inside dotted line show those of TSOP

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V _{cc}	Supply voltage	With respect to GND	- 0.3*~4.6	V
V _I	Input voltage		- 0.3*~V _{cc} + 0.3 (Max 4.6)	V
V _O	Output voltage		0~V _{cc}	V
P _d	Power dissipation	T _a =25°C	700	mW
T _{opr}	Operating temperature		- 40~85	°C
T _{stg}	Storage temperature		- 65~150	°C

* -3.0V in case of AC (Pulse width ≤ 30ns)

DC ELECTRICAL CHARACTERISTICS (T_a=- 40~85°C, V_{cc}=2.7~3.6V, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{IH}	High-level input voltage		2.0		V _{cc} + 0.3	V
V _{IL}	Low-level input voltage		-0.3*		0.6	V
V _{OH1}	High-level output voltage 1	I _{OH} = - 0.5mA	2.4			V
V _{OH2}	High-level output voltage 2	I _{OH} = - 0.05mA	V _{cc} - 0.5			V
V _{OL}	Low-level output voltage	I _{OL} = 2mA			0.4	V
I _I	Input current	V _I =0~V _{cc}			±1	μA
I _O	Output current in off-state	S ₁ =V _{IH} or S ₂ =V _{IL} or $\overline{OE}=V_{IH}$ V _{I/O} =0~V _{cc}			±1	μA
I _{CC1}	Active supply current	S ₁ =V _{IL} , S ₂ =V _{IH} , other inputs=V _{IH} or V _{IL} Output-open(duty 100%)	70ns		35	mA
I _{CC2}	Active supply current		100ns		30	
I _{CC3}	Stand-by current		1MHz		5	
I _{CC4}	Stand-by current	S ₁ =V _{IH} or S ₂ =V _{IL} , other inputs=0~V _{cc}			0.33	mA

* -3.0V in case of AC (Pulse width ≤ 30ns)

CAPACITANCE (T_a=- 40~85°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
C _I	Input capacitance	V _I =GND, V _I =25mVrms, f=1MHz			8	pF
C _O	Output capacitance	V _O =GND, V _O =25mVrms, f=1MHz			10	pF

Note 3: Direction for current flowing into an IC is positive (no mark).

4: Typical value is V_{cc} = 3V, T_a = 25°C

AC ELECTRICAL CHARACTERISTICS (Ta= 40~85°C, unless otherwise noted)

(1) MEASUREMENT CONDITIONS

V_{CC} 2.7~3.6V
 Input pulse level V_{IH}=2.2V, V_{IL}=0.4V
 Input rise and fall time 5ns
 Reference level V_{OH}=V_{OL}=1.5V
 Output loads Fig.1, CL=30pF
 CL=5pF (for t_{en}, t_{dis})
 Transition is measured ± 500 mV from steady state voltage. (for t_{en}, t_{dis})

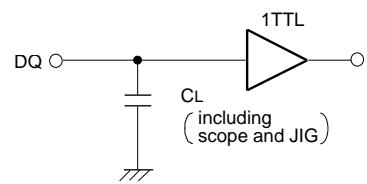


Fig.1 Output load

(2) READ CYCLE

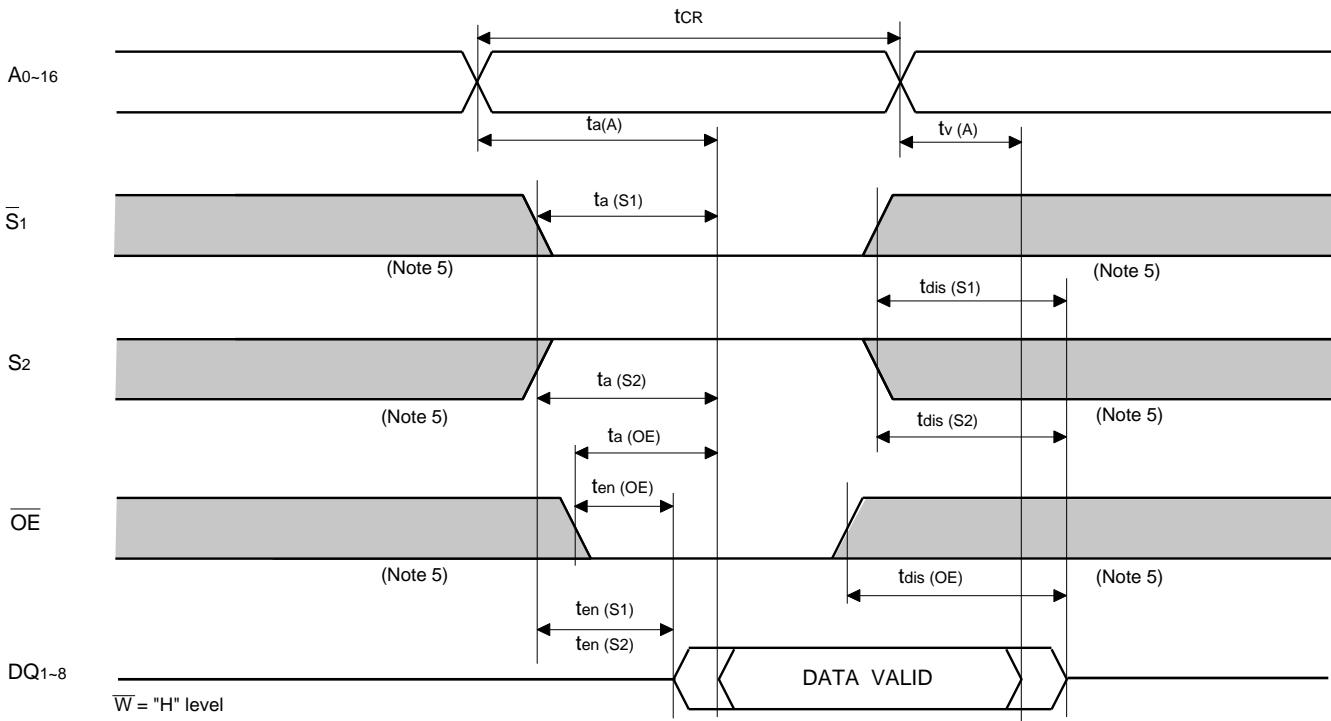
Symbol	Parameter	Limits		Unit	
		-70HI			
		Min	Max		
t _{CR}	Read cycle time	70		ns	
t _{a(A)}	Address access time		70	ns	
t _{a(S1)}	Chip select 1 access time		70	ns	
t _{a(S2)}	Chip select 2 access time		70	ns	
t _{a(OE)}	Output enable access time		35	ns	
t _{dis(S1)}	Output disable time after S ₁ high		25	ns	
t _{dis(S2)}	Output disable time after S ₂ low		25	ns	
t _{dis(OE)}	Output disable time after OE high		25	ns	
t _{en(S1)}	Output enable time after S ₁ low	10		ns	
t _{en(S2)}	Output enable time after S ₂ high	10		ns	
t _{en(OE)}	Output enable time after OE low	5		ns	
t _{V(A)}	Data valid time after address	10		ns	

(3) WRITE CYCLE

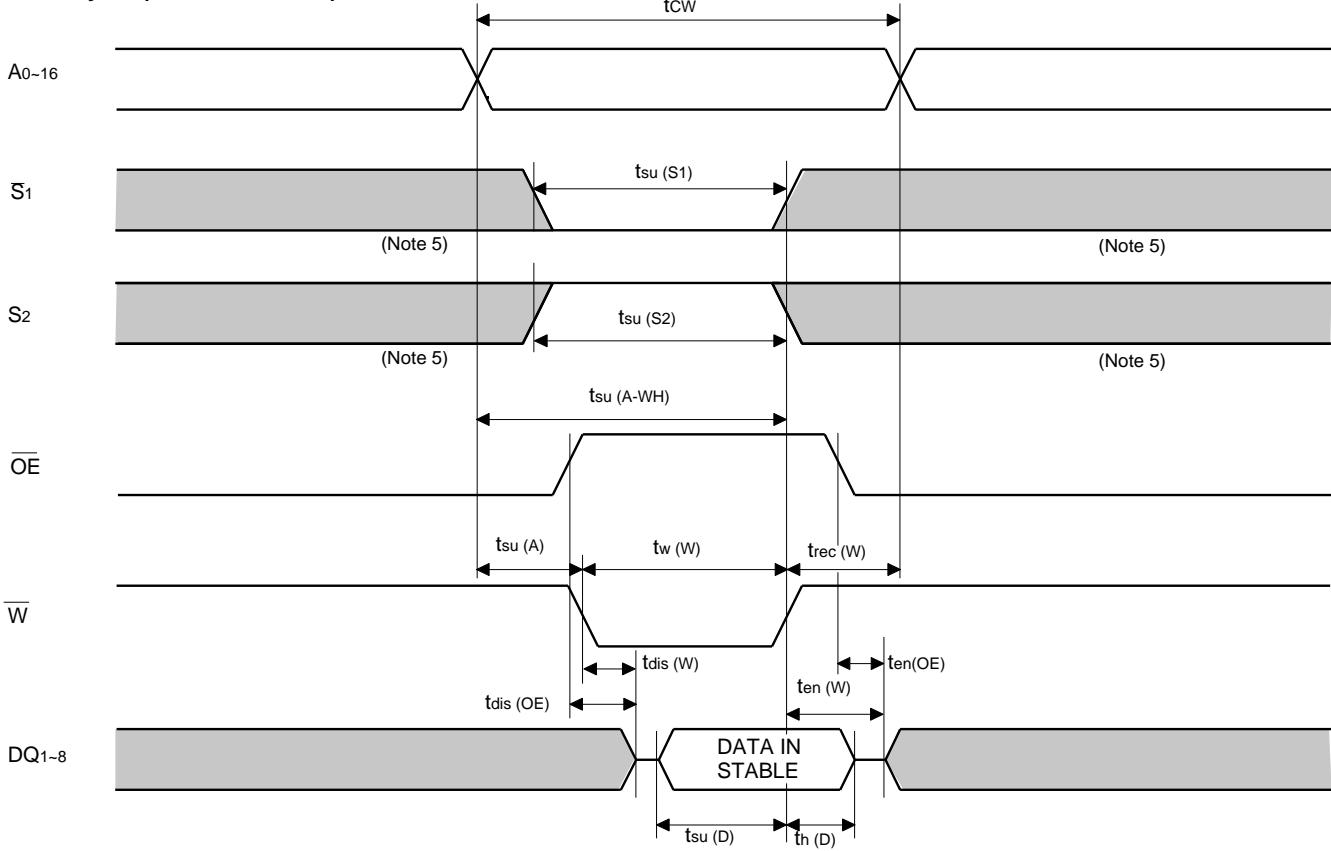
Symbol	Parameter	Limits		Unit	
		-70HI			
		Min	Max		
t _{CW}	Write cycle time	70		ns	
t _{w(W)}	Write pulse width	55		ns	
t _{su(A)}	Address setup time	0		ns	
t _{su(A-WH)}	Address setup time with respect to W	65		ns	
t _{su(S1)}	Chip select 1 setup time	65		ns	
t _{su(S2)}	Chip select 2 setup time	65		ns	
t _{su(D)}	Data setup time	30		ns	
t _{h(D)}	Data hold time	0		ns	
t _{rec(W)}	Write recovery time	0		ns	
t _{dis(W)}	Output disable time from W low		25	ns	
t _{dis(OE)}	Output disable time from OE high		25	ns	
t _{en(W)}	Output enable time from W high	5		ns	
t _{en(OE)}	Output enable time from OE low	5		ns	

(4) TIMING DIAGRAMS

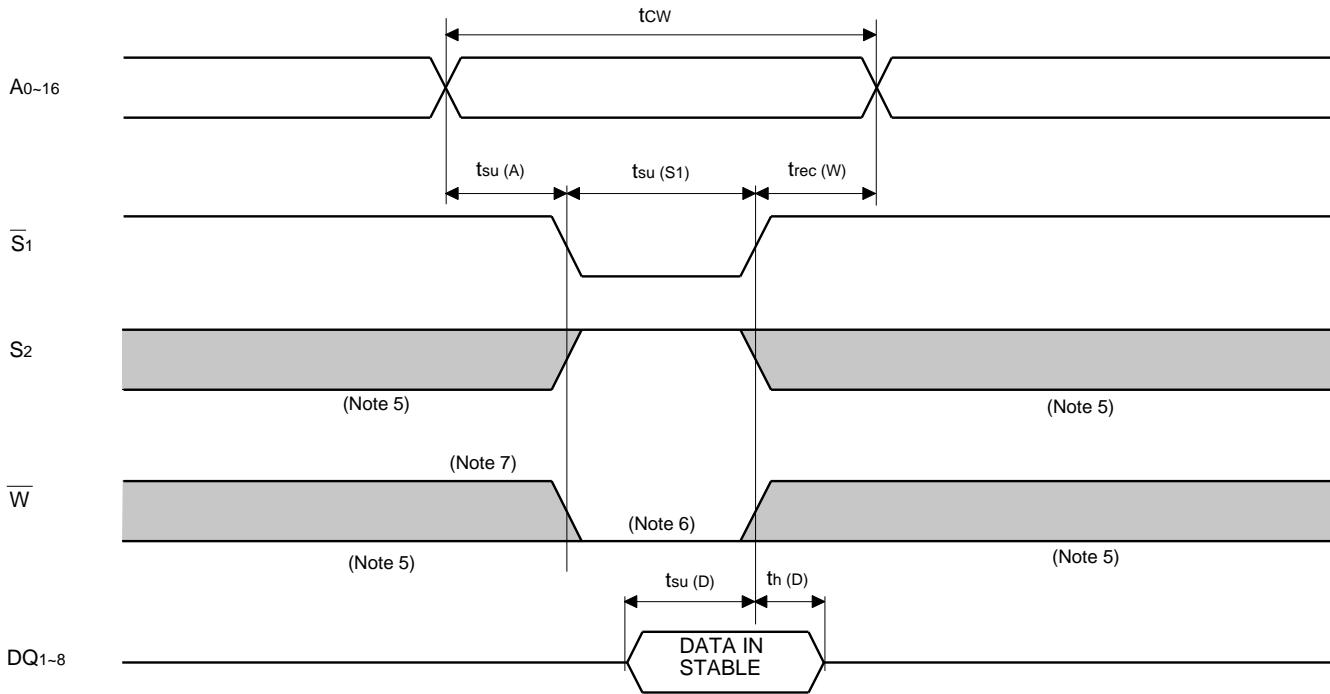
Read cycle



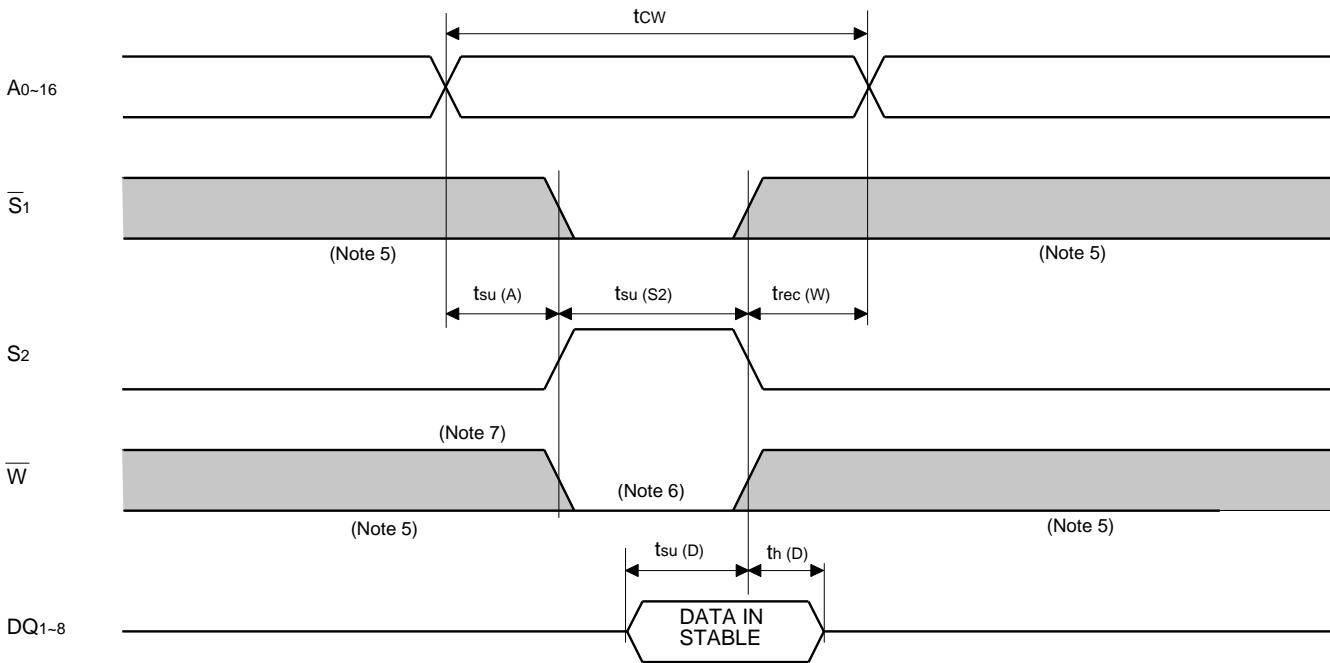
Write cycle (W control mode)



Write cycle ($\overline{S_1}$ control mode)



Write cycle (S2 control mode)



Note 5: Hatching indicates the state is "don't care".

6: Writing is executed while S_2 high overlaps \bar{S}_1 and \bar{W} low.

7: When the falling edge of \bar{W} is simultaneously or prior to the falling edge of \bar{S}_1 or rising edge of S_2 , the outputs are maintained in the high impedance state.

8: Don't apply inverted phase signal externally when DQ pin is output mode.

POWER DOWN CHARACTERISTICS

(1) ELECTRICAL CHARACTERISTICS (Ta= 40~85°C, unless otherwise noted)

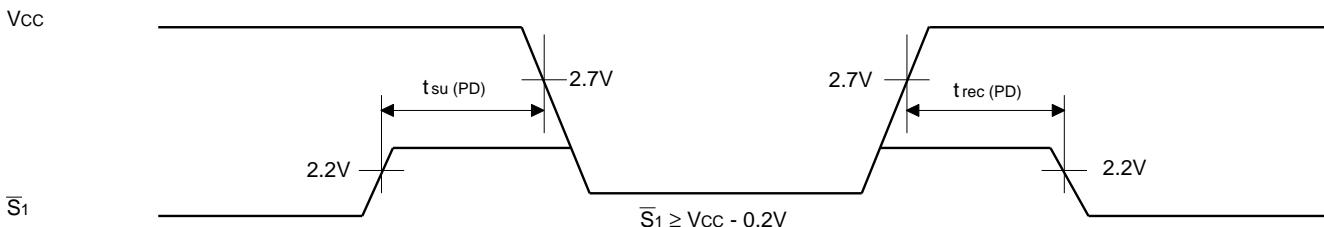
Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
V _{CC} (PD)	Power down supply voltage		2			V
V _I (S ₁)	Chip select input S ₁		2.0	V _{CC} (PD)		V
V _I (S ₂)	Chip select input S ₂	2.7V≤V _{CC} (PD) V _{CC} (PD)<2.7V			0.6 0.2	V
I _{CC} (PD)	Power down supply current	V _{CC} = 3V 1) S ₂ ≤ 0.2V, other inputs = 0~3V 2) S ₁ ≥ V _{CC} -0.2V, S ₂ ≥ V _{CC} -0.2V other inputs = 0~3V	-H1	-25°C -40°C -70°C -85°C	1 3 10 20	μA

(2) TIMING REQUIREMENTS (Ta= 40~85°C, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
t _{su} (PD)	Power down set up time		0			ns
t _{rec} (PD)	Power down recovery time		5			ms

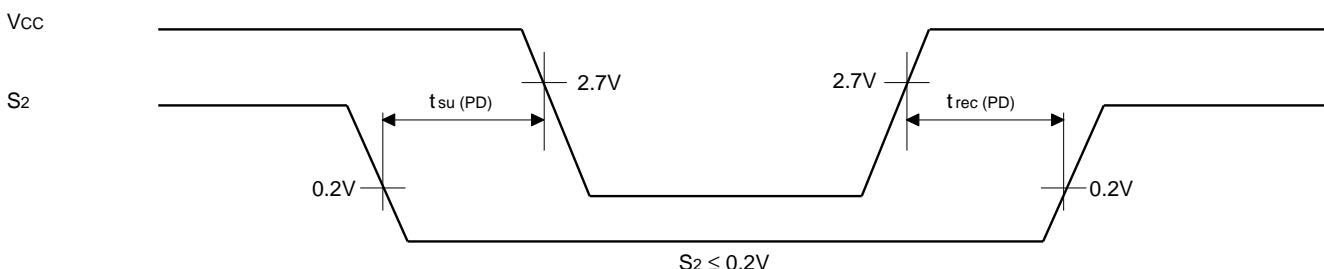
(3) POWER DOWN CHARACTERISTICS

S₁ control mode



Note 9: On the power down mode by controlling S₁, the input level of S₂ must be S₂≥ V_{CC} - 0.2V or S₂≤ 0.2V. The other pins(Address,I/O,WE,OE) can be in high impedance state.

S₂ control mode



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